

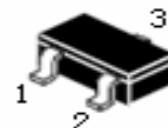
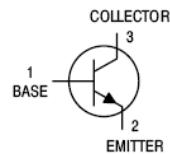


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## BFR380F

### Features

- Low leakage current
- Low capacitance characteristics
- Large dynamic range



**SOT-323**

### Mechanical Data

- Case: SOT-323
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BFR380F	SOT-323	3000 pcs / Tape & Reel	FCs

### Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	$V_{CBO}$	12	V
Collector-Emitter Breakdown Voltage	$V_{CEO}$	5	V
Emitter-Base Breakdown Voltage	$V_{EBO}$	2.5	V
Collector Current (continuous)	$I_C$	80	mA

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	$P_D$	380	mW
Junction Temperature Range	$T_J$	-55 ~ +150	°C
Storage Temperature Range	$T_{STG}$	-65 ~ +150	°C



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## Electrical Characteristics (@ T<sub>A</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0	12	-	-	V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	5	-	-	V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	2.5	-	-	V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 12V, I <sub>E</sub> = 0	-	-	100	nA
Collector Cut-off Current	I <sub>CEO</sub>	V <sub>CE</sub> = 5V, I <sub>B</sub> = 0	-	-	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 2.5V, I <sub>C</sub> = 0	-	-	1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA	80	100	200	-
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> = 15mA, V <sub>CE</sub> = 3V, f = 1GHz	11	-	-	GHz
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA f = 1.8GHz	-	11	-	dB
		V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA f = 3GHz	-	6.5	-	dB
Feed-Back Capacitance	C <sub>re</sub>	I <sub>C</sub> = i <sub>C</sub> = 0, V <sub>CB</sub> = 5V, f = 1MHz	-	0.2	-	pF
Collector Capacitance	C <sub>c</sub>	I <sub>E</sub> = i <sub>E</sub> = 0, V <sub>CB</sub> = 5V, f = 1MHz	-	0.47	0.7	pF
Emitter Capacitance	C <sub>e</sub>	I <sub>C</sub> = i <sub>C</sub> = 0, V <sub>EB</sub> = 0.5V, f = 1MHz	-	1	-	pF
Noise Figure	N <sub>F</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 8mA f = 1.8GHz	-	1.10	-	dB
Maximum Unilateral Power Gain	G <sub>UM</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA, f = 1.8GHz	-	13.5	-	dB
		V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA, f = 3.0GHz	-	9	-	dB
	I <sub>P3</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 40mA Z <sub>S</sub> = Z <sub>L</sub> = 50Ω, f = 1.8GHz		29		dBm



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## Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

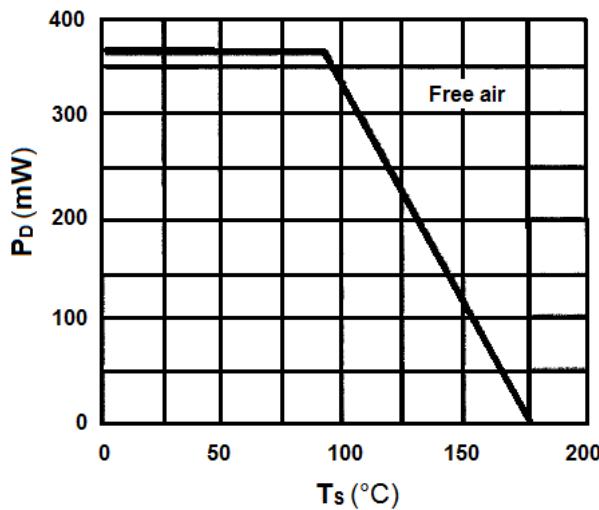


Fig. 1 Total Power Dissipation vs.  
Ambient Temperature

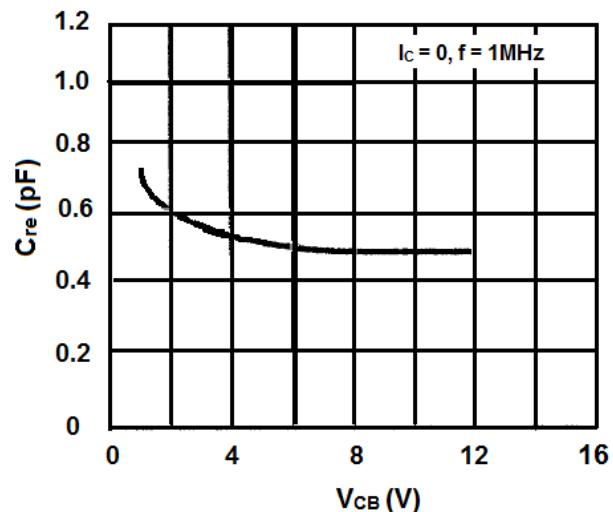


Fig. 2 Reverse Transfer Capacitance vs.

Collector to Base Voltage

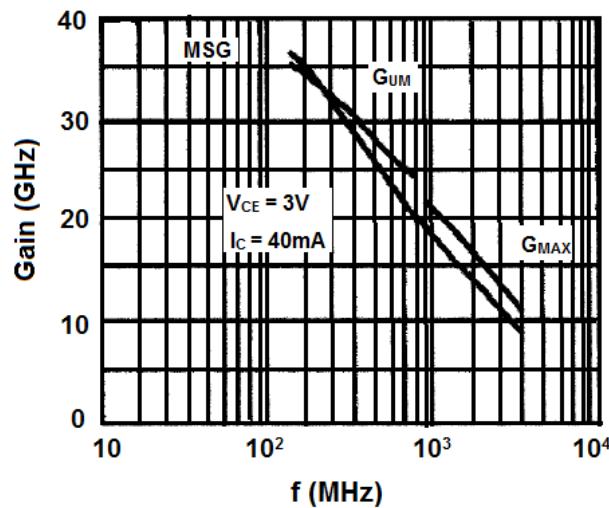


Fig. 3 Gain vs. Function of Frequency

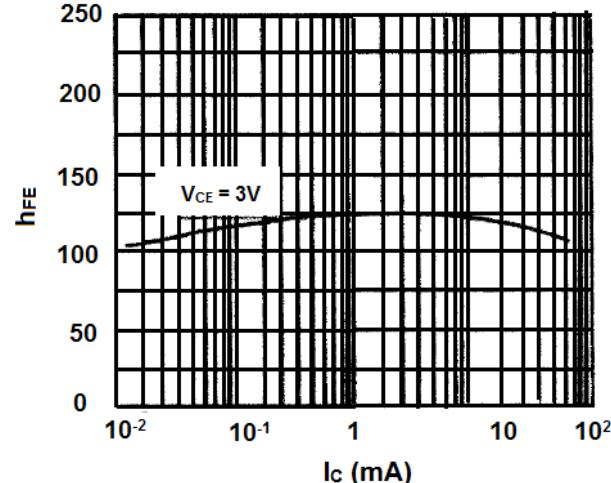


Fig. 4 DC Current vs. Collector Current



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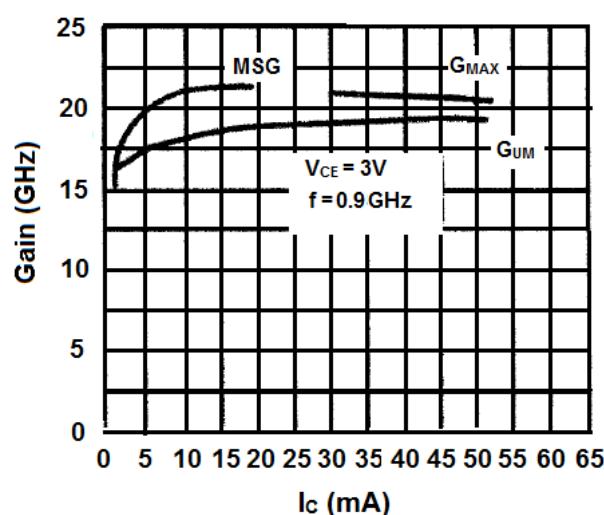


Fig. 5 Gain vs. Function of Collector Current

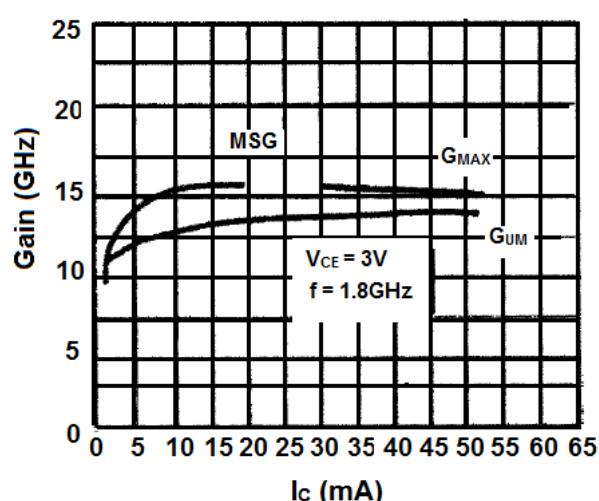


Fig. 6 Gain vs. Function of Collector Current

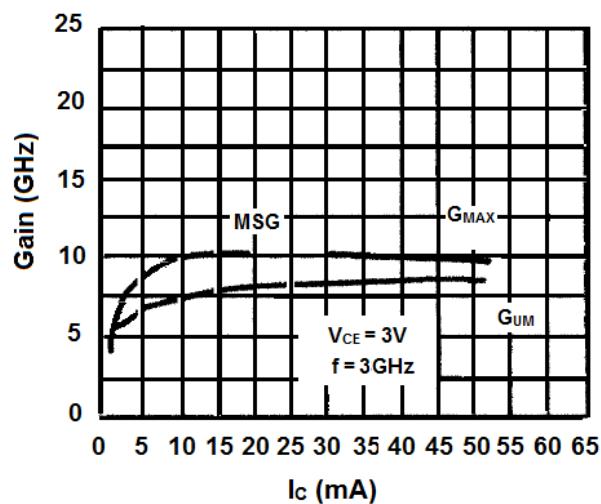


Fig. 7 Gain vs. Function of Collector Current

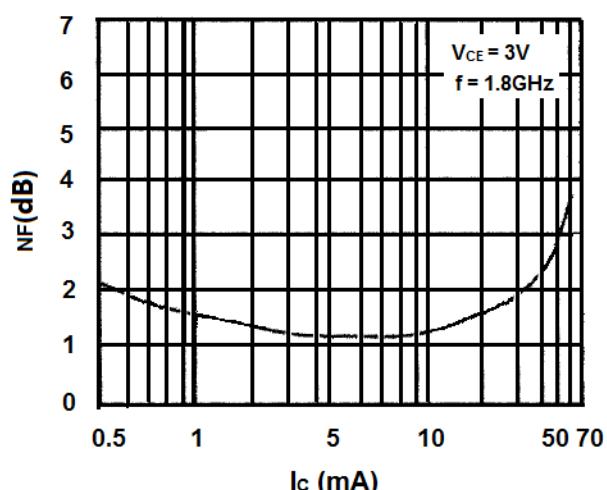
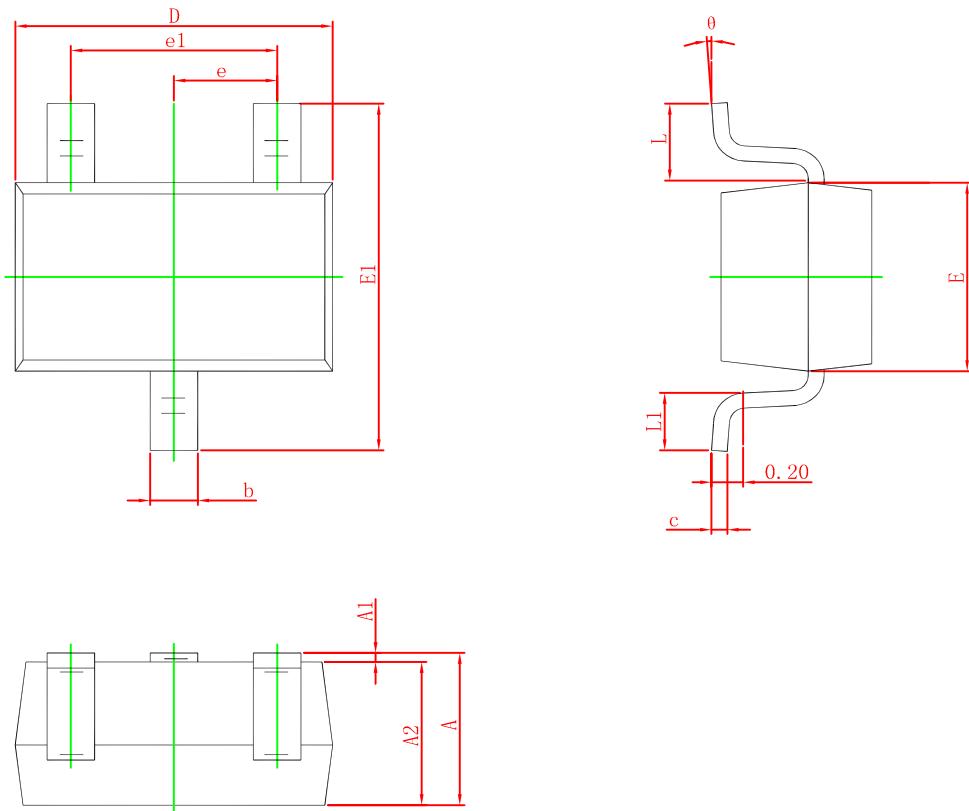


Fig. 8 Noise Figure vs. Collector Current



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### SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°